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Title: **JP5819777A2: SEMICONDUCTOR NONVOLATILE MEMORY STORAGE**

Country: **JP Japan**
Kind: **A**

Inventor: **MATSUO RYUICHI;**

Assignee: **MITSUBISHI ELECTRIC CORP**
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Published / Filed: **1983-11-17 / 1982-05-12**

Application Number: **JP1982000082006**

IPC Code: **H01L 29/78; G11C 11/40; H01L 27/10;**

Priority Number: **1982-05-12 JP1982000082006**

Abstract:

PURPOSE: To provide the memory region with which information can be stored even when ultraviolet rays are irradiated by a method wherein an ultraviolet ray type FET for nonvolatile memory, having a floating gate and a control gate, is arranged in matrix form, and at least one of the above is covered by an ultraviolet ray shielding film.

CONSTITUTION: An N type source 2 and a drain 3 are provided on a P type Si substrate 1, a floating gate 4 and a control gate are provided and an FAMOS type FET of N-channel is arranged in matrix form as a memory element. At least one of them is covered by an Al film 8 and prevent the infiltration of ultraviolet ray 7 using it. As a result, the information once written-in can be maintained at this part even when ultraviolet rays are irradiated. Accordingly, the established information is memorized in this region, thereby enabling to prevent the elimination of information by the ultraviolet rays irradiated after an unexpected writing-in or the rewriting of other sections have been performed.

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Buy PDF	Patent	Pub.Date	Inventor	Assignee	Title
	US5070378	1991-12-03	Yamagata; Yasushi	NEC Corporation	EPROM erasable by UV radiation redundant circuit
	US4942450	1990-07-17	Iwashita; Shinichi	NEC Corporation	Semiconductor memory device having volatile memory transistors
	US4758984	1988-07-19	Yoshida; Masanobu	Fujitsu Limited	Semiconductor memory device including read only memory element for storing information